NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE4009S uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge . The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

General Features

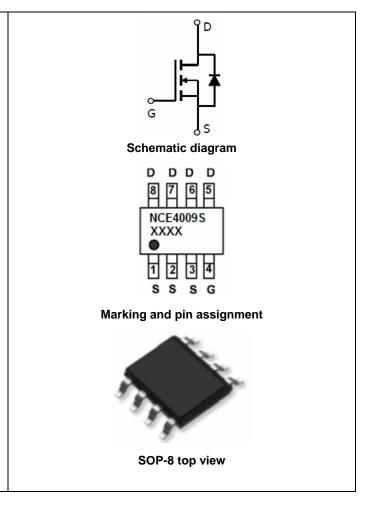
N-Channel

 $V_{DS} = 40V, I_{D} = 9A$

 $R_{DS(ON)}$ < 16m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ < 24m Ω @ V_{GS} =4.5V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4009S	NCE4009S	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	9	Α
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	6.4	Α
Pulsed Drain Current	I _{DM}	40	Α
Maximum Power Dissipation	P _D	2	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	62.5	°C/W
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N-CH Electrical Characteristics (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	1	1.5	2.0	V
Drain Course On State Desistance	Б	V _{GS} =10V, I _D =8A	-	12.9	16	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =4A	-	40 1 1 ±100 - 12.9 16	mΩ	
Forward Transconductance	g FS	V _{DS} =5V,I _D =8A	33	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\\ -20\\\\ -0\\	-	964	-	PF
Output Capacitance	Coss	V_{DS} =20V, V_{GS} =0V, F=1.0MHz	-	109	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	96	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	5.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =20V, R_L =2.5 Ω	-	14	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =3 Ω	-	24	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	V _{DD} =20V, R _L =2.5Ω	-	22.9	-	nC
Gate-Source Charge	Q _{gs}	,- ,	-	3.5	-	nC
Gate-Drain Charge	Q_{gd}	v _{GS} -10v	-	5.3	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =9A	-	0.8	1.2	V



N- Channel Typical Electrical and Thermal Characteristics (Curves)

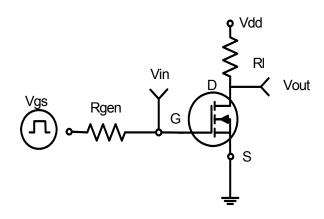


Figure 1:Switching Test Circuit

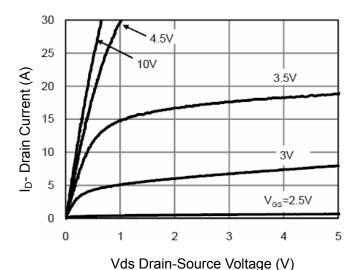


Figure 3 Output Characteristics

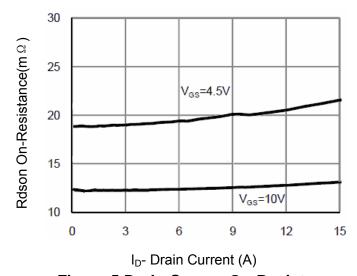


Figure 5 Drain-Source On-Resistance

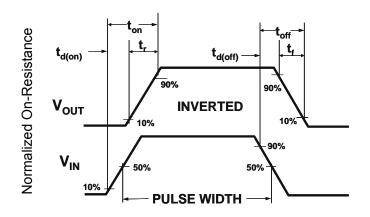


Figure 2:Switching Waveforms

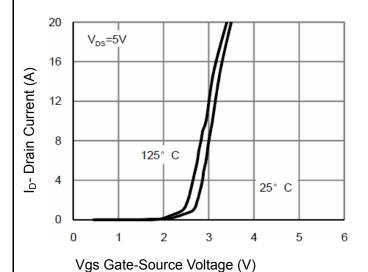


Figure 4 Transfer Characteristics

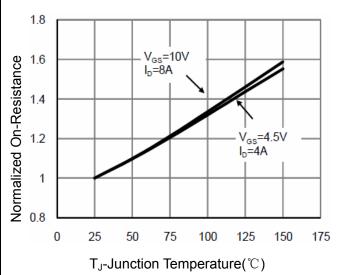
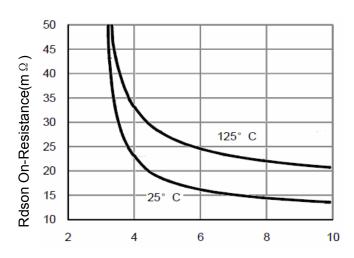


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V)



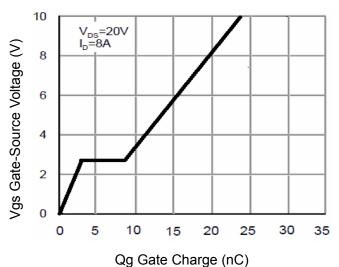


Figure 9 Gate Charge

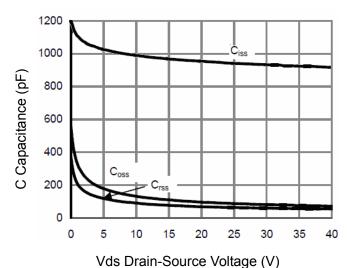
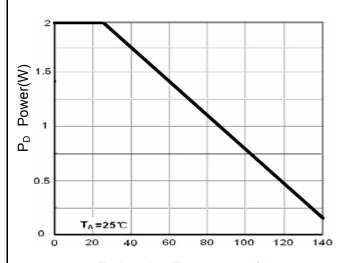
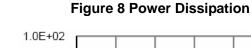
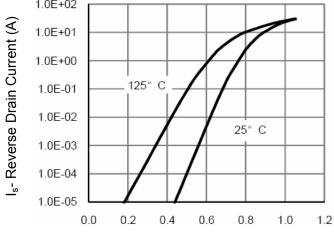


Figure 11 Capacitance vs Vds



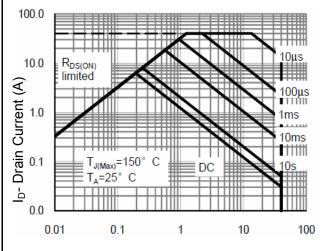
 T_J -Junction Temperature(${}^{\circ}\mathbb{C}$)





Vds Drain-Source Voltage (V)

Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area



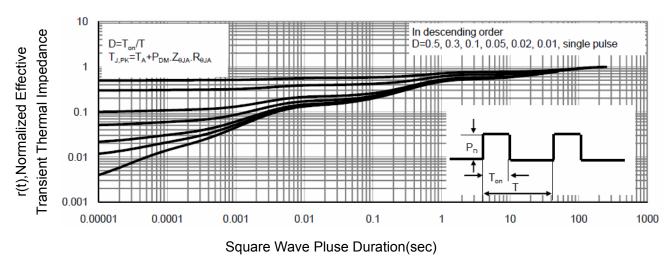
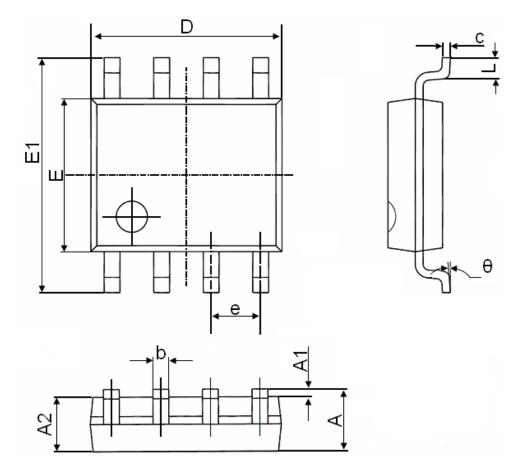


Figure 13 Normalized Maximum Transient Thermal Impedance

Pb Free Product



SOP-8 Package Information



Cumbal	Dimensions	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270(BSC)		0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



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NCE4009S

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